

High-Speed CMOS Logic 8-Bit Parallel-In/Serial-Out Shift Register

Features

- Buffered Inputs
- Asynchronous Parallel Load
- Complementary Outputs
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

The 'HC165 and 'HCT165 are 8-bit parallel or serial-in shift registers with complementary serial outputs (Q_7 and $\overline{Q_7}$) available from the last stage. When the parallel load (\overline{PL}) input is LOW, parallel data from the D0 to D7 inputs are loaded into the register asynchronously. When the \overline{PL} is HIGH, data enters the register serially at the DS input and shifts one place to the right ($Q_0 \rightarrow Q_1 \rightarrow Q_2$, etc.) with each positive-going clock transition. This feature allows parallel-to-serial converter expansion by tying the Q_7 output to the DS input of the succeeding device.

For predictable operation the LOW-to-HIGH transition of \overline{CE} should only take place while CP is HIGH. Also, CP and \overline{CE} should be LOW before the LOW-to-HIGH transition of PL to prevent shifting the data when \overline{PL} goes HIGH.

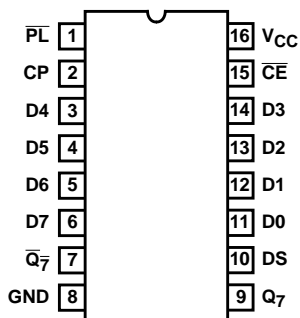
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC165F3A	-55 to 125	16 Ld CERDIP
CD54HCT165F3A	-55 to 125	16 Ld CERDIP
CD74HC165E	-55 to 125	16 Ld PDIP
CD74HC165M	-55 to 125	16 Ld SOIC
CD74HC165MT	-55 to 125	16 Ld SOIC
CD54HC165M96	-55 to 125	16 Ld SOIC
CD74HCT165E	-55 to 125	16 Ld PDIP
CD74HCT165M	-55 to 125	16 Ld SOIC
CD74HCT165MT	-55 to 125	16 Ld SOIC
CD54HCT165M96	-55 to 125	16 Ld SOIC

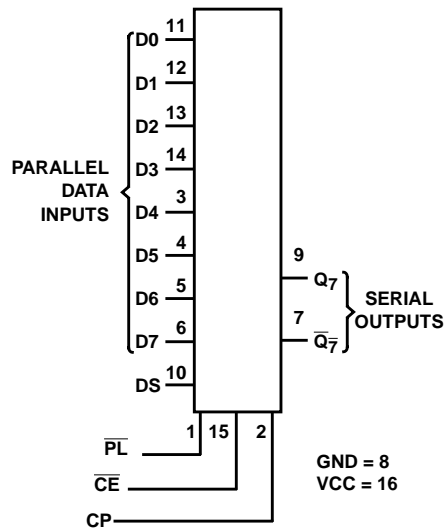
NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel. The suffix T denotes a small-quantity reel of 250.

Pinout

CD54HC165, CD54HCT165
(CERDIP)
CD74HC165, CD74HCT165
(PDIP, SOIC)
TOP VIEW



Functional Diagram



TRUTH TABLE

OPERATING MODE	INPUTS					Q _n REGISTER		OUTPUTS	
	\overline{PL}	\overline{CE}	CP	DS	D0 - D7	Q ₀	Q ₁ - Q ₆	Q ₇	$\overline{Q_7}$
Parallel Load	L	X	X	X	L	L	L-L	L	H
	L	X	X	X	H	H	H-H	H	L
Serial Shift	H	L	↑	l	X	L	q ₀ - q ₅	q ₆	$\overline{q_6}$
	H	L	↑	h	X	H	q ₀ - q ₅	q ₆	$\overline{q_6}$
Hold Do Nothing	H	H	X	X	X	q ₀	q ₁ - q ₆	q ₇	$\overline{q_7}$

H = High Voltage Level
 h = High Voltage Level One Set-up Time Prior To The Low-to-high Clock Transition
 l = Low Voltage Level One Set-up Time Prior To The Low-to-high Clock Transition
 L = Low Voltage Level
 X = Don't Care
 ↑ = Transition from Low to High Level
 q_n = Lower Case Letters Indicate The State Of the Reference Output Clock Transition

CD54HC165, CD74HC165, CD54HCT165, CD74HCT165

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current per Output, I_O	
For $V_O < -0.5V$ $V_O > V_{CC} + 0.5V$	$\pm 25mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC} or I_{GND}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
E (PDIP) Package	67
M (SOIC) Package	73
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA

CD54HC165, CD74HC165, CD54HCT165, CD74HCT165

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 2)	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

- For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
DS, D0 to D7	0.35
CP, \overline{PL}	0.65

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. 360μA max at 25°C.

Prerequisite For Switching Specifications

PARAMETER	SYMBOL	V _{CC} (V)	25°C		-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	
HC TYPES									
CP Pulse Width	t _{WL} , t _{WH}	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns

CD54HC165, CD74HC165, CD54HCT165, CD74HCT165

Prerequisite For Switching Specifications (Continued)

PARAMETER	SYMBOL	V _{CC} (V)	25°C		-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	
$\overline{\text{PL}}$ Pulse Width	t_{WL}	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Set-up Time DS to CP	t_{SU}	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
$\overline{\text{CE}}$ to CP	$t_{\text{SU(L)}}$	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
D0-D7 to $\overline{\text{PL}}$	t_{SU}	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Hold Time DS to CP or $\overline{\text{CE}}$	t_{H}	2	35	-	45	-	55	-	ns
		4.5	7	-	9	-	11	-	ns
		6	6	-	8	-	9	-	ns
$\overline{\text{CE}}$ to CP	t_{H}	2	0	-	0	-	0	-	ns
		4.5	0	-	0	-	0	-	ns
		6	0	-	0	-	0	-	ns
Recovery Time $\overline{\text{PL}}$ to CP	t_{REC}	2	100	-	125	-	150	-	ns
		4.5	20	-	25	-	30	-	ns
		6	17	-	21	-	26	-	ns
Maximum Clock Pulse Frequency	f_{MAX}	2	6	-	5	-	4	-	MHz
		4.5	30	-	24	-	20	-	MHz
		6	35	-	28	-	24	-	MHz

HCT TYPES

CP Pulse Width	$t_{\text{WL}}, t_{\text{WH}}$	4.5	18	-	23	-	27	-	ns
$\overline{\text{PL}}$ Pulse Width	t_{WL}	4.5	20	-	25	-	30	-	ns
Set-up Time DS to CP	t_{SU}	4.5	20	-	25	-	30	-	ns
$\overline{\text{CE}}$ to CP	$t_{\text{SU(L)}}$	4.5	20	-	25	-	30	-	ns
D0-D7 to $\overline{\text{PL}}$	t_{SU}	6	20	-	25	-	30	-	ns
Hold Time DS to CP or $\overline{\text{CE}}$	t_{H}	4.5	7	-	9	-	11	-	ns
$\overline{\text{CE}}$ to CP	$t_{\text{S}}, t_{\text{H}}$	4.5	0	-	0	-	0	-	ns
Recovery Time $\overline{\text{PL}}$ to CP	t_{REC}	4.5	20	-	25	-	30	-	ns
Maximum Clock Pulse Frequency	f_{MAX}	4.5	27	-	22	-	18	-	MHz

CD54HC165, CD74HC165, CD54HCT165, CD74HCT165

Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay CP or \overline{CE} to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	2	-	165	205	250	ns
			4.5	-	33	41	50	ns
		C _L = 15pF	5	13	-	-	-	ns
			C _L = 50pF	6	-	28	35	43
\overline{PL} to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	2	-	175	220	265	ns
			4.5	-	35	44	53	ns
		C _L = 15pF	5	14	-	-	-	ns
			C _L = 50pF	6	-	30	37	45
D7 to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
		C _L = 15pF	5	12	-	-	-	ns
			C _L = 50pF	6	-	26	33	38
Output Transition Times	t_{TLH}, t_{THL}	C _L = 50pF	2	-	75	95	110	ns
			4.5	-	15	19	22	ns
			6	-	13	16	19	ns
Input Capacitance	C _{IN}	-	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	17	-	-	-	pF
HCT TYPES								
Propagation Delay CP or \overline{CE} to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	4.5	-	40	50	60	ns
		C _L = 15pF	5	17	-	-	-	ns
\overline{PL} to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	4.5	-	40	50	60	ns
		C _L = 15pF	5	17	-	-	-	ns
D7 to Q ₇ or $\overline{Q_7}$	t_{PLH}, t_{PHL}	C _L = 50pF	4.5	-	35	44	53	ns
		C _L = 15pF	5	14	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	C _L = 50pF	4.5	-	15	19	22	ns
Input Capacitance	C _{IN}	C _L = 50pF	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	24	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per package.
- $P_D = V_{CC}^2 f_i + \sum (C_L V_{CC}^2 + f_o)$ where f_i = Input Frequency, f_o = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

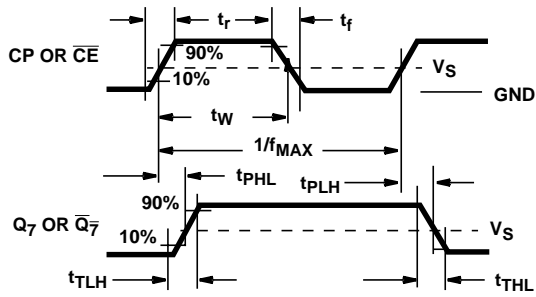


FIGURE 3. SERIAL-SHIFT MODE

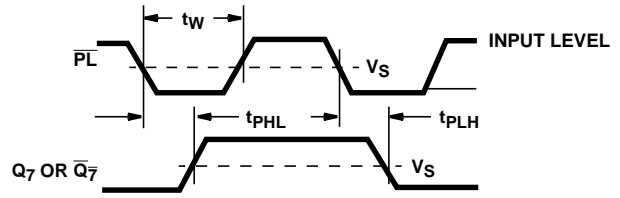


FIGURE 4. PARALLEL-LOAD MODE

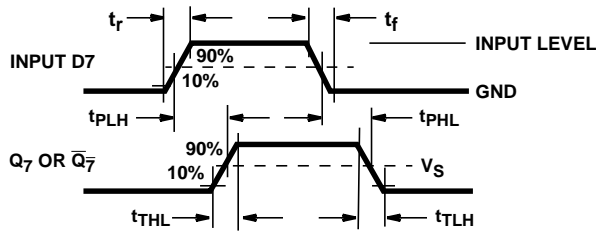


FIGURE 5. PARALLEL-LOAD MODE

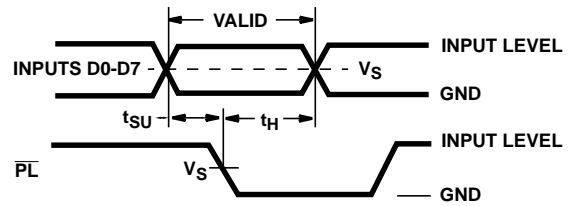


FIGURE 6. PARALLEL-LOAD MODE

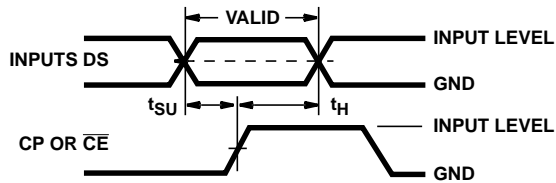


FIGURE 7. SERIAL-SHIFT MODE

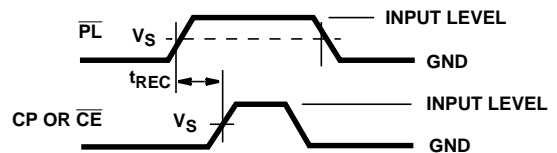


FIGURE 8. SERIAL-SHIFT MODE

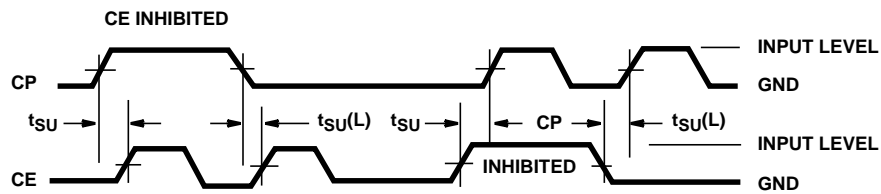


FIGURE 9. SERIAL-SHIFT, CLOCK-INHIBIT MODE